


Pin Definition:

1. Gate
2. Source
3. Drain

PRODUCT SUMMARY

V_{DS} (V)	R_{DS(on)} (max)	I_D (mA)
60	2 @ V _{GS} = 10V	300
	4 @ V _{GS} = 4.5V	200

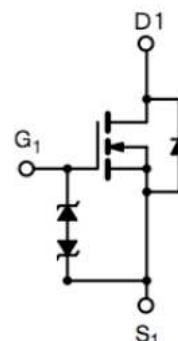
Features

- Low On-Resistance
- ESD Protected 2KV
- High Speed Switching
- Low Voltage Drive

Ordering Information

Part No.	Package	Packing
TSM2N7002KCX RFG	SOT-23	3kpcs / 7" Reel

Note: "G" denotes for Halogen Free

Block Diagram


N-Channel MOSFET

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current	Continuous @ T _A =25°C	I _D	300
	Pulsed	I _{DM}	800
Drain Reverse Current	Continuous @ T _A =25°C	I _{DR}	300
	Pulsed	I _{DMR}	800
Maximum Power Dissipation	P _D	300	mW
Operating Junction Temperature	T _J	+150	°C
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit
Lead Temperature (1/8" from case)	T _L	5	S
Junction to Ambient Thermal Resistance (PCB mounted)	R _{θJA}	350	°C/W

Notes:

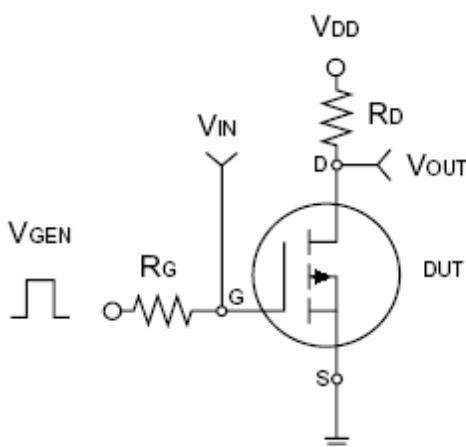
- a. Pulse width ≤300μs, Duty cycle ≤2%
- b. When the device is mounted on a glass epoxy board with area measuring 1 x 0.75 x 0.62 inch.
- c. The power dissipation of the package may result in a continuous drain current.

Electrical Specifications ($T_A=25^\circ\text{C}$, unless otherwise noted)

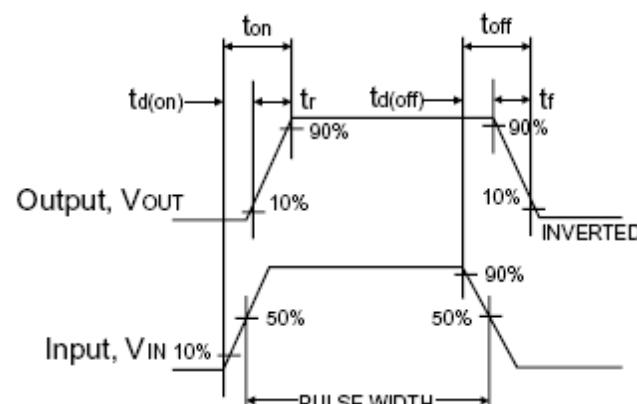
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$	BV_{DSS}	60	--	--	V
Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	$V_{GS(\text{TH})}$	1.0	1.5	2.5	V
Gate Body Leakage	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$	I_{GSS}	--	--	± 10	μA
Zero Gate Voltage Drain Current	$V_{DS}=60\text{V}$, $V_{GS}=0\text{V}$	I_{DSS}	--	--	1.0	μA
Drain-Source On-State Resistance	$V_{GS}=10\text{V}$, $I_D=300\text{mA}$	$R_{DS(\text{ON})}$	--	1.2	2	Ω
	$V_{GS}=4.5\text{V}$, $I_D=200\text{mA}$		--	2	4	
Forward Transconductance	$V_{DS}=10\text{V}$, $I_D=200\text{mA}$	g_{fs}	100	--	--	mS
Diode Forward Voltage	$I_S=300\text{mA}$, $V_{GS}=0\text{V}$	V_{SD}	--	0.8	1.4	V
Dynamic^b						
Total Gate Charge	$V_{DS}=10\text{V}$, $I_D=250\text{mA}$, $V_{GS}=4.5\text{V}$	Q_g	--	0.4	0.6	nC
Input Capacitance	$V_{DS}=25\text{V}$, $V_{GS}=0\text{V}$, $f=1.0\text{MHz}$	C_{iss}	--	30	--	pF
Output Capacitance		C_{oss}	--	6	--	
Reverse Transfer Capacitance		C_{rss}	--	2.5	--	
Switching^c						
Turn-On Delay Time	$V_{DD}=30\text{V}$, $R_G=10\Omega$	$t_{d(on)}$	--	--	25	ns
Turn-Off Delay Time		$t_{d(off)}$	--	--	35	

Notes:

- a. pulse test: PW $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.



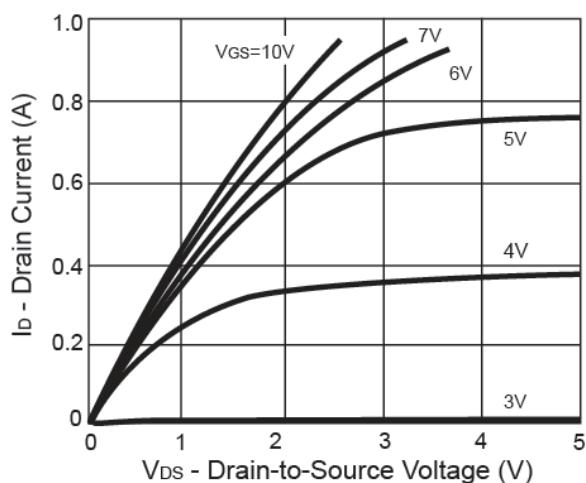
Switching Test Circuit



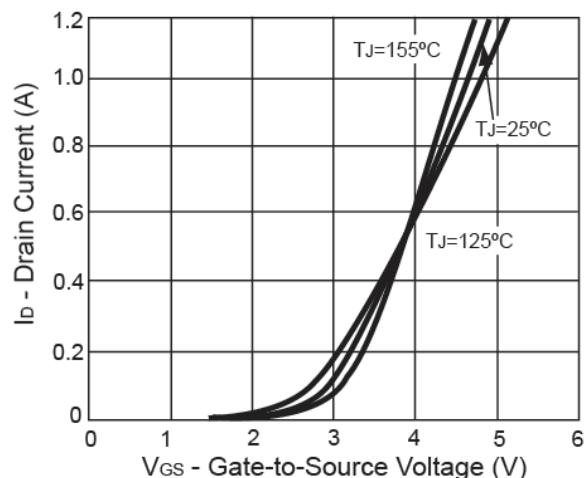
Switching Waveforms

Electrical Characteristics Curve ($T_A=25^\circ\text{C}$, unless otherwise noted)

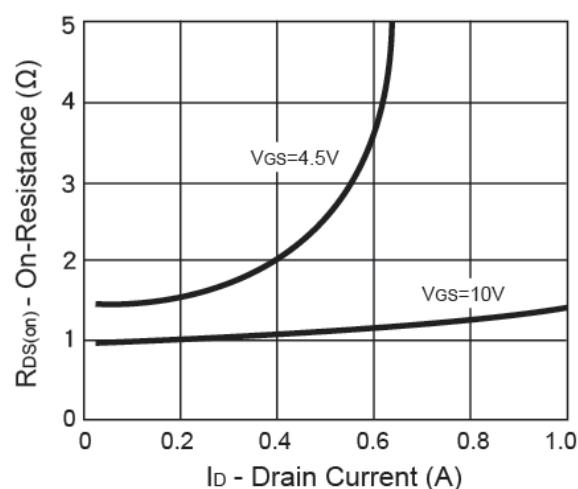
Output Characteristics



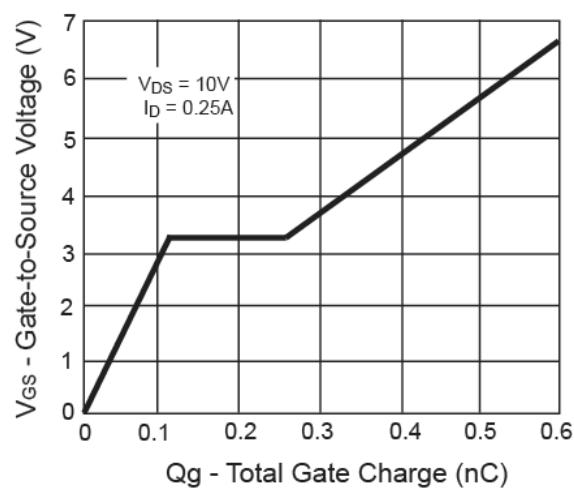
Transfer Characteristics



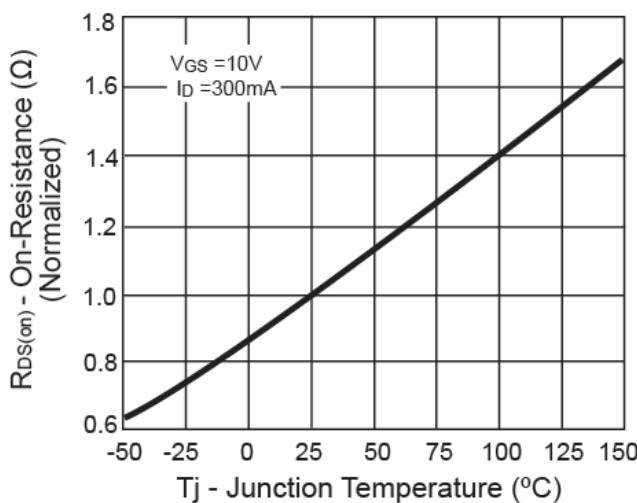
On-Resistance vs. Drain Current



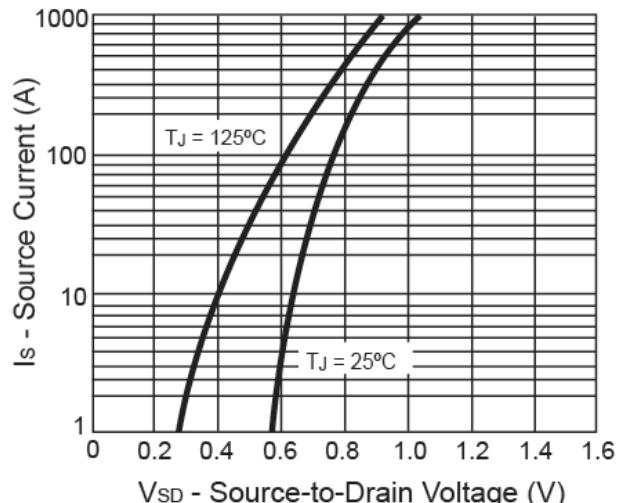
Gate Charge



On-Resistance vs. Junction Temperature

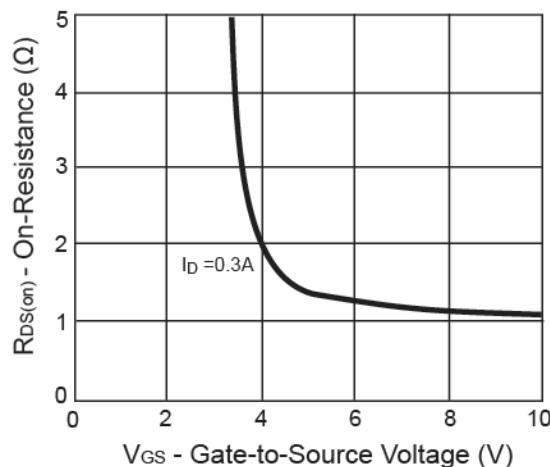


Source-Drain Diode Forward Voltage

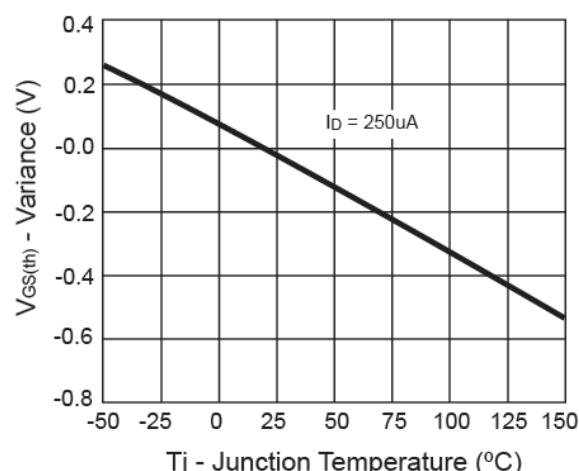


Electrical Characteristics Curve ($T_a = 25^\circ\text{C}$, unless otherwise noted)

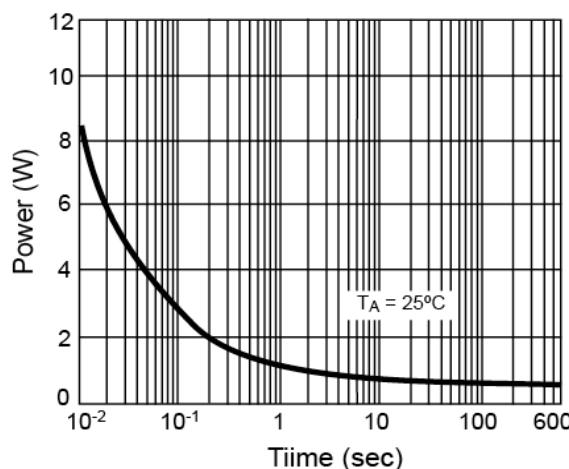
On-Resistance vs. Gate-Source Voltage



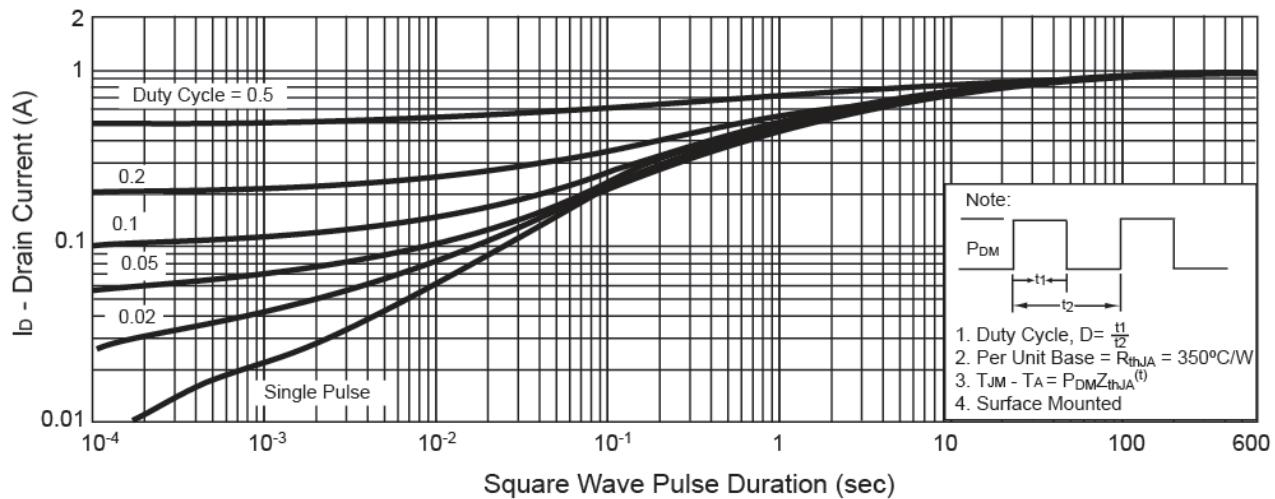
Threshold Voltage



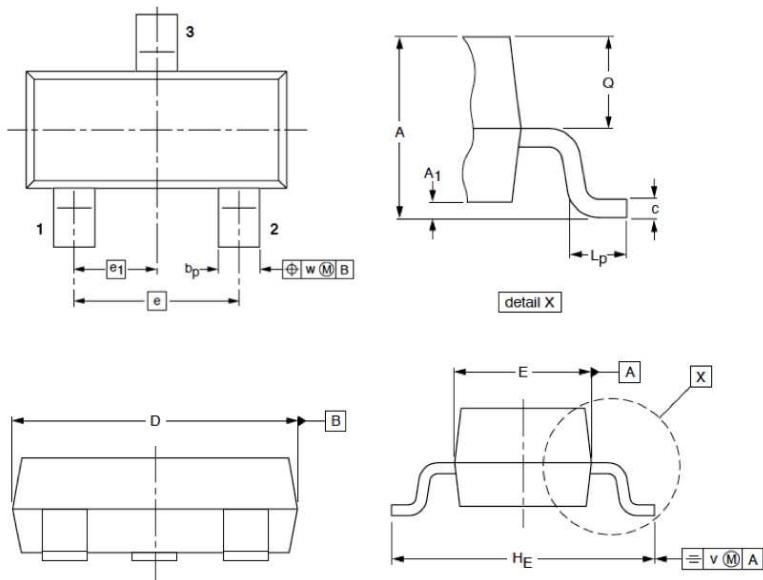
Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient

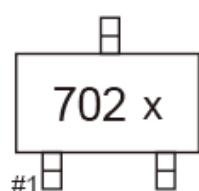


SOT-23 Mechanical Drawing



SOT-23 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.00	BSC	0.039	BSC
A1	--	0.10	--	0.004
bp	0.37	0.42	0.014	0.016
C	0.09	0.15	0.004	0.005
D	2.80	3.00	0.110	0.118
E	1.20	1.40	0.047	0.055
e	1.9 BSC		0.075 BSC	
e1	0.95 BSC		0.037 BSC	
H _E	2.35	2.45	0.093	0.096
L _P	0.15	0.45	0.005	0.018
Q	0.45	0.55	0.018	0.022
V	0.2 BSC		0.007 BSC	
W	0.1 BSC		0.004 BSC	

Marking Diagram



702 = TSM2N7002KCX Device Code
x = Internal Code

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